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AMENDMENT UNDER 37 C.F.R. § 1.116  
EXPEDITED PROCEDURE  
GROUP 2826  
PATENT APPLICATION

2800  
2/14/03  
#102819  
Amend  
SDAVIS  
2/20/03

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re application of

Docket No: Q61743

Takashi UDAGAWA

Appln. No.: 09/885,943

Group Art Unit: 2826

Confirmation No.: 6215

Examiner: Johannes P. Mondt

Filed: June 22, 2001

For: GROUP-III NITRIDE SEMICONDUCTOR LIGHT-EMITTING DEVICE AND  
PRODUCTION METHOD THEREOF

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**AMENDMENT UNDER 37 C.F.R. § 1.116**

**ATTN: BOX AF**

Commissioner for Patents  
Washington, D.C. 20231

Sir:

This Amendment is submitted in response to the Office Action dated November 14, 2002. Please amend the above-identified application as follows:

**IN THE CLAIMS:**

**Please cancel claims 17, 18 and 21 without prejudice or disclaimer.**

**Please enter the following amended claims:**

B<sup>1</sup>  
1. (Twice Amended) A group-III nitride semiconductor light-emitting device comprising a single crystal substrate having thereon a light-emitting part structure comprising a gallium nitride phosphide ( $\text{GaN}_{1-x}\text{P}_x$ , wherein  $0 < x < 1$ ) single crystal layer provided via a boron phosphide (BP)-based buffer layer, wherein the boron phosphide-based buffer layer comprises a